
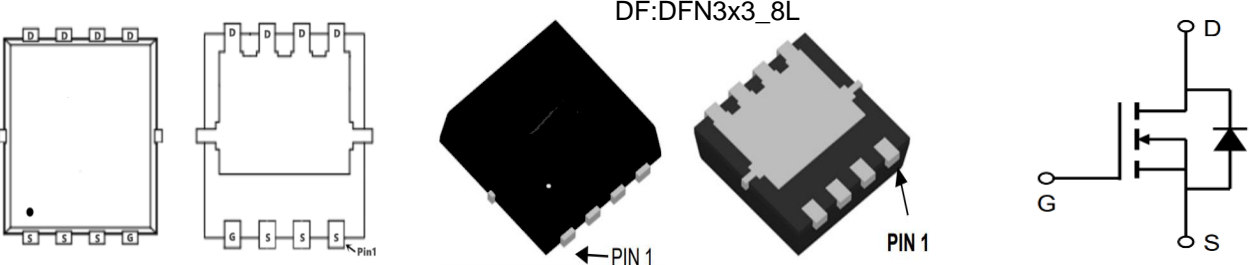
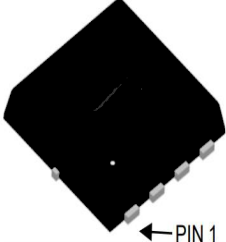
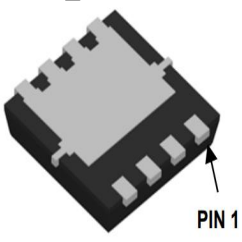
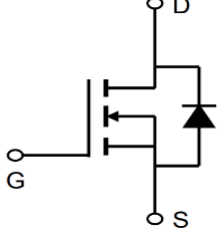


TM20N03DF

N-Channel Enhancement Mosfet

<p>General Description</p> <ul style="list-style-type: none"> • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant <p>Applications</p> <ul style="list-style-type: none"> • Load switch • PWM 	<p>General Features</p> <p>$V_{DS} = 30V$ $I_D = 20A$</p> <p>$R_{DS(ON)} = 15\text{ m}\Omega$ (typ.) @ $V_{GS} = 10V$</p> <p>100% UIS Tested 100% R_g Tested</p> 
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DF:DFN3x3_8L

Marking: 20N03

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	30		V
V_{GS}	Gate-Source Voltage	± 20		V
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	20		A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	8		A
I_{DM}	Pulsed Drain Current ²	38		A
EAS	Single Pulse Avalanche Energy ³	28		mJ
I_{AS}	Avalanche Current	13.8		A
$P_D @ T_C = 25^\circ\text{C}$	Total Power Dissipation ⁴	5.5		W
T_{STG}	Storage Temperature Range	-55 to 175		$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 175		$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	36	$^\circ\text{C}/\text{W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V,$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	$V_{GS}=10V, I_D=5A$	-	15	20	m Ω
		$V_{GS}=4.5V, I_D=3A$	-	21	29	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V,$ $f=1.0MHz$	-	490	-	pF
C_{oss}	Output Capacitance		-	79	-	pF
C_{rss}	Reverse Transfer Capacitance		-	61	-	pF
Q_g	Total Gate Charge	$V_{DS}=15V, I_D=5.8A,$ $V_{GS}=10V$	-	10	-	nC
Q_{gs}	Gate-Source Charge		-	1.7	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	2.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=15V, I_D=3A,$ $V_{GS}=10V, R_{REN}=3\Omega$	-	6	-	ns
t_r	Turn-on Rise Time		-	15	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	17	-	ns
t_f	Turn-off Fall Time		-	17	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	20	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	36	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=9A$	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F=5A, di/dt=100A/\mu s$	-	7	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	2	-	nC

- Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
 2. EAS condition : $T_J=25^\circ\text{C}, V_{DD}=15V, V_G=10V, L=0.5mH, R_g=25\Omega, I_{AS}=6A$
 3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

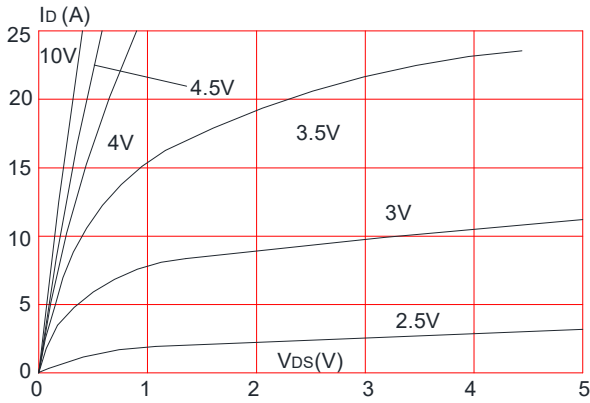


Figure 2: Typical Transfer Characteristics

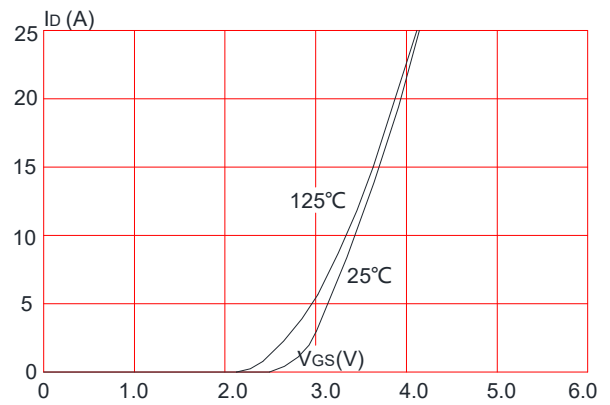


Figure 3: On-resistance vs. Drain Current

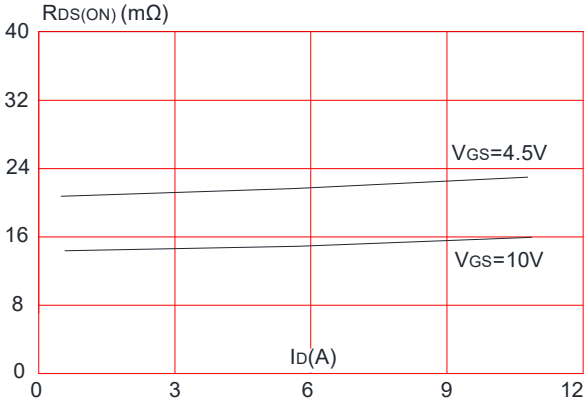


Figure 4: Body Diode Characteristics

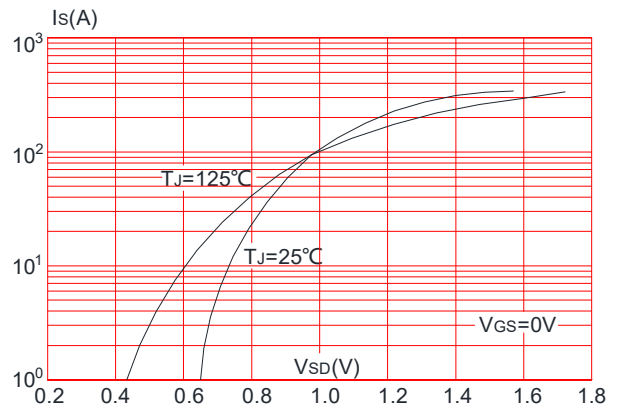


Figure 5: Gate Charge Characteristics

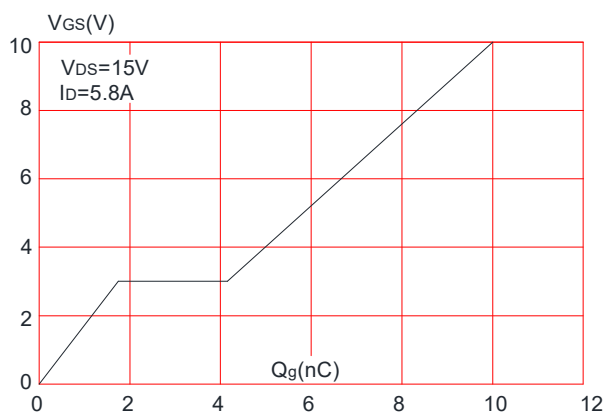
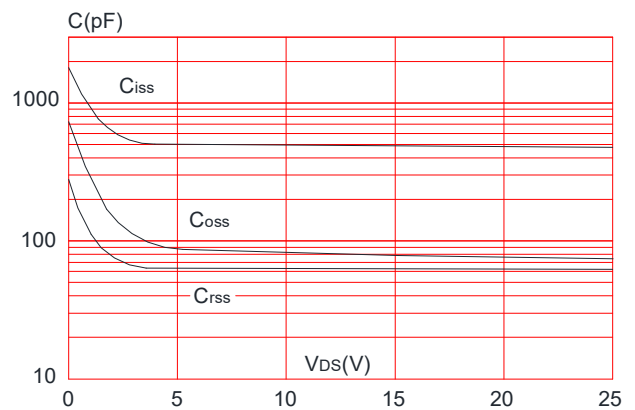


Figure 6: Capacitance Characteristics



TM20N03DF

N-Channel Enhancement Mosfet

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

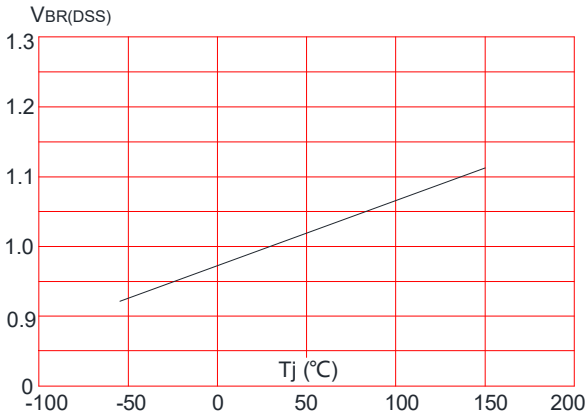


Figure 8: Normalized on Resistance vs. Junction Temperature

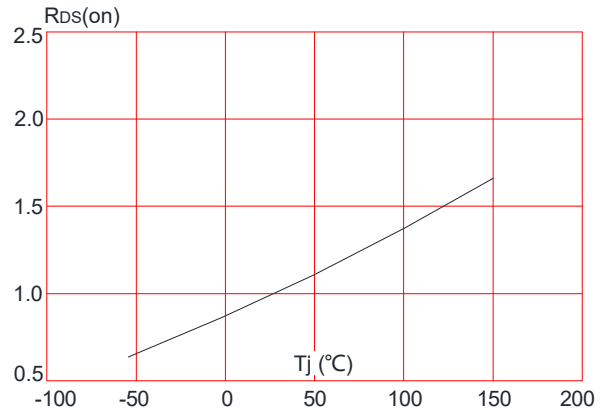


Figure 9: Maximum Safe Operating Area

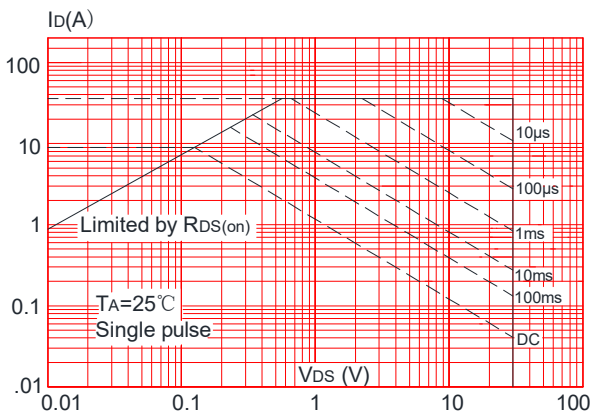


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

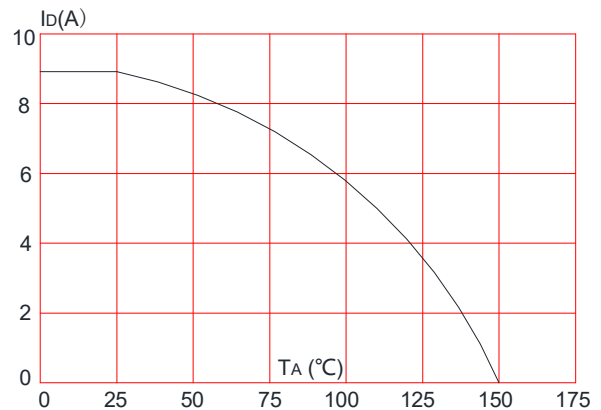
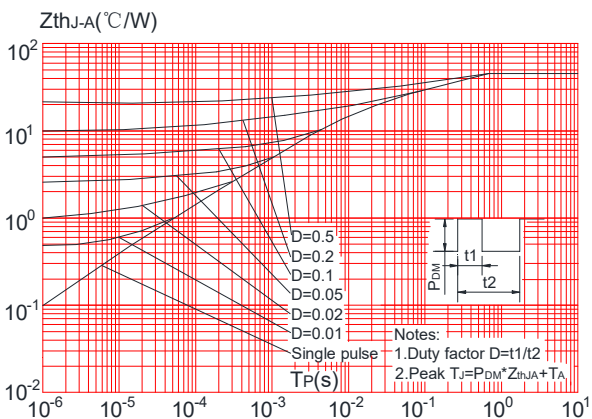


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Test Circuit

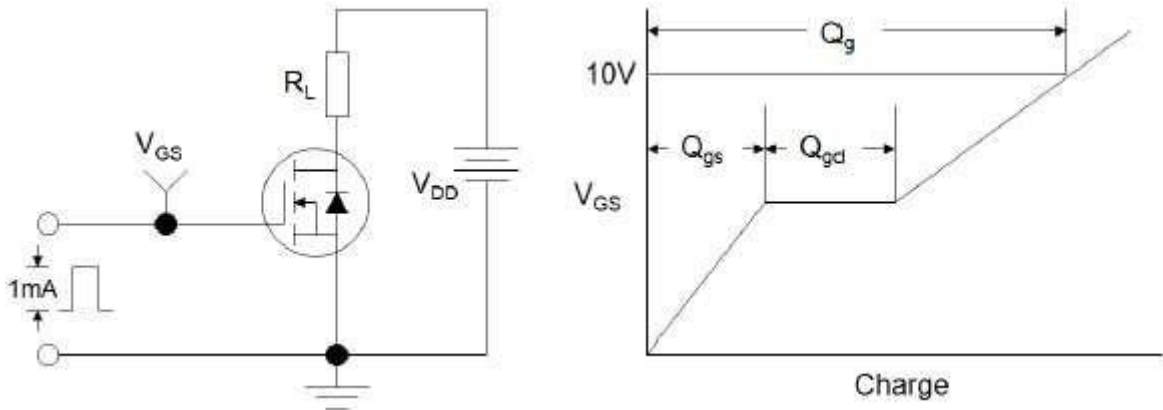


Figure1:Gate Charge Test Circuit & Waveform

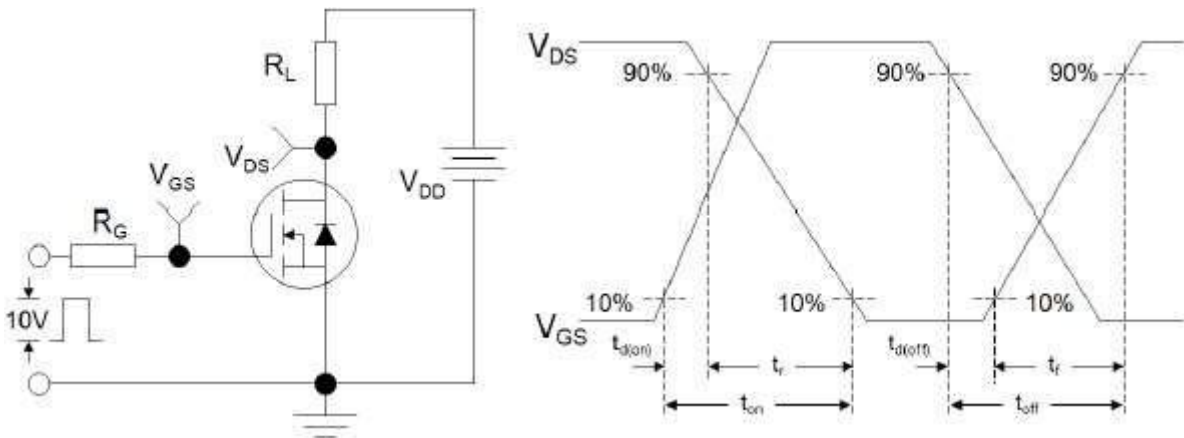


Figure 2: Resistive Switching Test Circuit & Waveforms

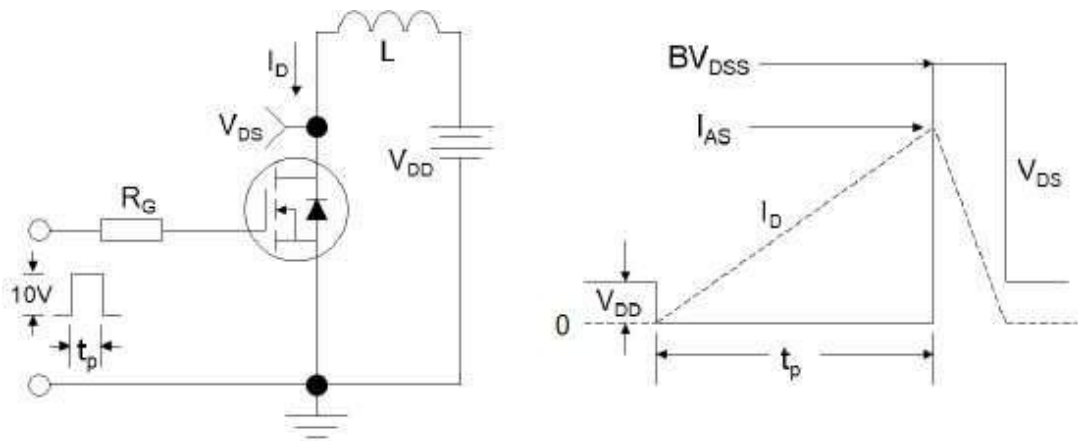
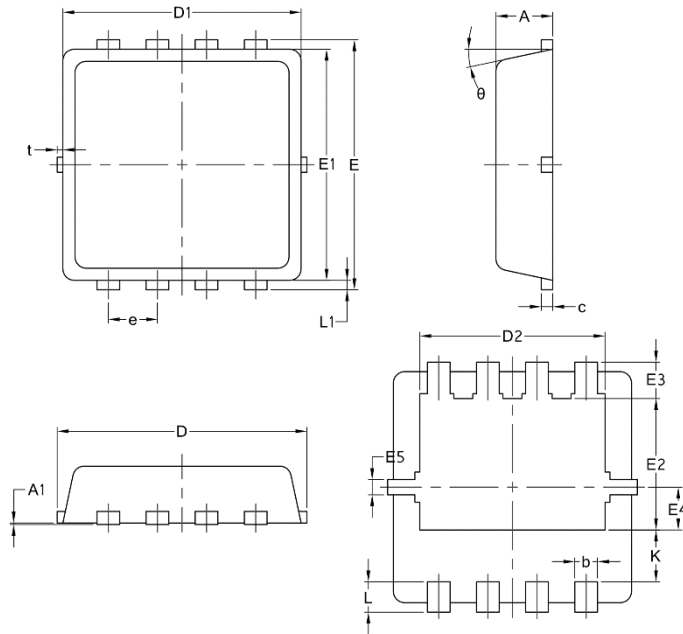


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Package Mechanical Data:DFN3x3–8L



Symbol	Common		
	mm		
	Mim	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.20	0.30	0.40
c	0.10	0.152	0.25
D	3.15	3.30	3.45
D1	3.00	3.15	3.25
D2	2.29	2.45	2.65
E	3.15	3.30	3.45
E1	2.90	3.05	3.20
E2	1.54	1.74	1.94
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.59	0.69	0.89
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
t	0	0.075	0.13
Φ	10	12	14

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